

ABSTRACT OF THE DISCLOSURE

Disclosed is a method for manufacturing a semiconductor device which efficiently carries out a process on a semiconductor substrate, such as dry etching, and cleaning for removing a foreign matter after the process. The method includes a step of removing a foreign matter by using both an electric action of a plasma generated by plasma generation means and a physical action caused by a frictional stress of a fast gas stream formed by a pad structure which is arranged close to a wafer surface.

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